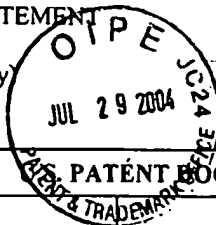


FORM PTO-1449

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Patent and Trademark OfficeAtty. Docket No.
P25051Application No.
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2877

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SN	4 5 4 7 0 7 3	10/15/85	KUGIMIYA			

FOREIGN PATENT DOCUMENTS

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SN	0 2 / 2 9 8 3 5	05/25/00	W.I.P.O			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SN	1	Yang, "An Optical Imaging Method for Wafer Warpage Measurements," <i>Journal of the Electrochemical Society</i> , Vol. 132, No. 5, pp. 1214 – 1218 (1985).
	2	"Optical Shop Testing," ed. Malacara, John Wiley & Sons, New York pp. 323 – 349 (1979).
	3	Riesz, "Geometrical Optical Model of the Image Formation in Makyoh (Magic Mirror) Topography," <i>J.Phys.D: Appl.Phys.</i> , Vol. 33, pp. 3033 – 3040, XP002229672 UK (2000).
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	5	Reisz, "Makyoh Topography for the Morphological Study of Compound Semiconductor Wafer and Structures," <i>Material Science & Engineering</i> , Vol. B80, pp. 220 – 223, XP002229676 NL (2001).
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	7	Laczik, "Quantitative Makyoh Topography," <i>Proc. Annual ACM Symp. On Principles of Distributed Computing</i> , Vol. 3743, pp. 151 – 156, XP000874538 (May 1999).
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	9	Koehler, "Plane-wave X-ray Topography and its Application to Semiconductor Problems," <i>Journal of Materials Science, Material in Electronics</i> , Chapman and Hall, London GB, pp. 167 – 174, XP000912483, ISSN: 0957-4522 (May 3, 1999).
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EXAMINER

Sanghyun

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1/25/05

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.